



Amendments to the Claims:

This Listing of Claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-16 (canceled).

17. (previously presented) A method of making a semiconductor device comprising:

- (a) sealing the semiconductor device in a package by surrounding it with thermosetting resin and thermally curing the resin at a first temperature;
- (b) baking the thermosetting resin at a second temperature not higher than the first temperature; and
- (c) further baking the thermosetting resin at a third temperature higher than the first temperature.

18. (previously presented) A method as in claim 17 wherein step (b) advances curing of the thermosetting resin.

19. (previously presented) A method as in claim 17 wherein the second temperature is between about 220°C and about 260°C.

20. (previously presented) A method as in claim 17 further comprising a step of inspecting the semiconductor device.

21. (previously presented) A method as in claim 17 wherein the semiconductor device comprises an integrated circuit.

22. (previously presented) A method as in claim 17 wherein step (a) includes a transfer molding process.

23. (previously presented) A method as in claim 17 wherein step (a) includes a potting process.

24. (previously presented) A method of making a semiconductor device comprising:

- (a) sealing the semiconductor device in a package by surrounding it with thermosetting resin and thermally curing the resin at a first temperature;
- (b) baking the thermosetting resin at a second temperature not higher than the first temperature; and
- (c) further baking the thermosetting resin at a third temperature higher than the first temperature; and
- (d) inspecting the semiconductor device.

25. (previously presented) A method as in claim 24 wherein a conductive lead is adhesively affixed to a main surface of the semiconductor device.

26. (previously presented) A method as in claim 25 wherein the conductive lead is adhesively affixed to a peripheral portion of the main surface of the semiconductor device.

27. (previously presented) A method as in claim 26 wherein an electrode of the semiconductor device is electrically connected to the conductive lead.

28. (previously presented) A method of making a semiconductor device comprising:

- (a) sealing the semiconductor device in a package by surrounding it with thermosetting resin and curing the resin;
- (b) baking the thermosetting resin at a temperature not higher than a temperature at which the resin was cured in step (a);
- (c) further baking the thermosetting resin at a third temperature higher than the temperature at which the resin was cured in step (a); and
- (d) inspecting the semiconductor device.

29. (currently amended) A method of making a electronic apparatus comprising:

~~preparing a semiconductor device by mounting it on a substrate with a solder;~~
preparing a semiconductor device by sealing ~~it~~ a semiconductor chip in a resin and curing the resin;

baking the semiconductor device at a temperature not more higher than the temperature at which the resin ~~was cured~~is cured; and then

baking the semiconductor device at a temperature more higher than the temperature at which the resin ~~was cured~~is cured;

inspecting a characteristic of the semiconductor chip; and then
mounting the semiconductor device on a substrate with a solder to make the
electronic apparatus.

30. (previously presented) A method as in claim 29 wherein the solder does not contain lead.